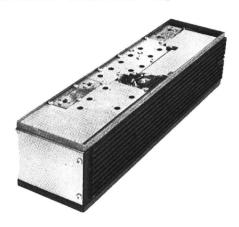
MASTR Progress Line

25-50 MHz RECEIVER MODELS 4ER39C10-27



SPECIFICATIONS

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-dB SINAD (EIA Method) 20-dB Quieting Method

Selectivity

EIA Two-Signal Method 20-dB Quieting Method

Spurious Response

First Oscillator Stability

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Maximum Squelch

Intermodulation (EIA)

Maximum Frequency Separation

Frequency Response

ER-39-C

25-50 MHz

5 watts at less than 5% distortion

 $0.25 \mu V$ $0.35 \mu V$

-85 dB (adjacent channel, 20 kHz channels) -100 dB at ± 15 kHz

-100 dB

 $\pm .0005\%$ (-30°C to +60°C)

±7 kHz (narrow-band)

 $0.15 \mu V$ Greater than 20 dB quieting (less than

 $1.5 \mu V)$

-60 dB

0.4%

+1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz (1000-Hz reference)

*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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---- WARNING ---

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

DESCRIPTION

General Electric MASTR Progress Line Receiver Type ER-39-C is a double conversion, superheterodyne FM receiver designed for operation on the 25-50 megahertz band.

The receiver is of single-unit construction and is completely housed in a copper-plated aluminum casting for maximum shielding and rigidity. The top compartment of the casting contains the RF, oscillator, converter, and 1st IF amplifier stages. The bottom portion of the casting contains the IF-audio and squelch board, and the optional Channel Guard Board.

CIRCUIT ANALYSIS

The MASTR Progress Line Receiver is completely transistorized, using silicon

transistors throughout for added reliability. Input leads to the receiver are individually filtered by the 20-pin feed-through by-pass connector J443. A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set Model 4EX3A10 or 4EX8K10, 11 for ease of alignment and servicing. The Test Set meters the oscillator, multiplier, and limiter stages as well as the discriminator and regulated 10 volts.

RF AMPLIFIER (A341)

RF Amplifier (A341) consists of two high-Q helical resonators and an RF amplifier stage (Q1). The RF signal from the antenna is coupled by RF cable W441 to a tap on L341/L343/L345. The tap is positioned to

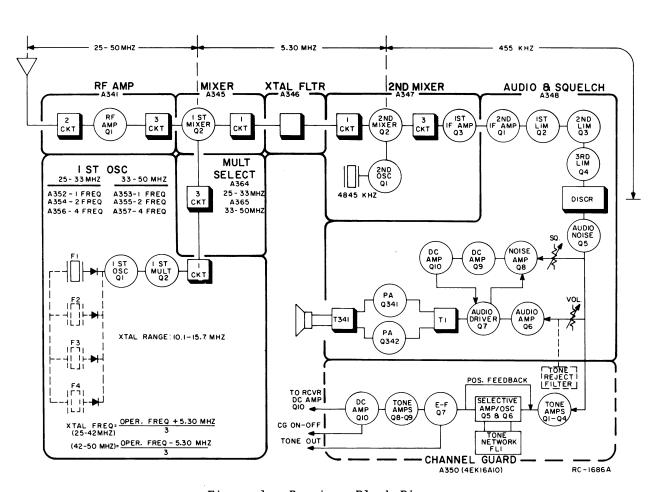


Figure 1 - Receiver Block Diagram

insure the proper impedance match to the antenna. RF energy is coupled through the two coils by an opening in the shield wall to the base of RF Amplifier Ql. The coils are tuned to the incoming frequency by air trimmer capacitors C341 and C342. The output of Ql is coupled through three tuned circuits to the base of the first mixer.

1ST OSCILLATOR AND MULTIPLIER (A352-A357)

The receiver 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a fundamental mode at a frequency of approximately 10 to 15 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides ±.0005% frequency stability as soon as the receiver is energized—without the warm-up time required by crystal ovens or warmers.

In single frequency receivers, bias for the oscillator transistor is obtained by a jumper from Hl to H2 on the oscillator board.

In multi-frequency receivers, a diode is connected in series with the crystal, and up to three addition crystal circuits can be added. The 10-volt jumper is removed and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit.

Switching the +10 volts to the crystal circuit forward biases the diode and reduces its impedance. This applies the crystal frequency to the base of oscillator transistor Ql. Feedback for the oscillator is developed across C21/C22. The output is coupled to the base of 1st multiplier Q2.

The output of the 1st multiplier is transformer-coupled (T3/T4) to multiplier selectivity assembly A364/A365. The 1st multiplier tank is tuned to three times the crystal frequency and is metered at centralized metering jack J442-4 through metering network CR1, R1, C7 and C8.

MULTIPLIER SELECTIVITY ASSEMBLY (A364/A365)

Following the 1st multiplier tank (T3/T4) are three additional L-C tuned circuits (A364/A365-L1 -L2 and -L3). Capacitor C12/C16 couples the multiplier selectivity output to the base of the first mixer.

1ST MIXER (A345) AND CRYSTAL FILTER (A346)

The RF signal from the RF amplifier and the injection voltage from the 1st multiplier are applied to the base of 1st mixer A345-Q2. The mixer collector tank (L2 and C3) is tuned to 5.3 megahertz and

provides impedance matching to the high IF crystal filter.

A highly selective crystal filter (A346) following the 1st mixer provides the major selectivity for the receiver. The output of the filter is fed through impedance matching transformer A347-Tl to the base of the 2nd mixer.

2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A347)

A347-Q2 operates in a Colpitts oscillator circuit, with feedback supplied through C4. The oscillator low-side injection voltage (4845 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 455-kHz mixer output is applied to three tuned low IF circuits, L1, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier A347-Q3. The output of A347-Q3 is R-C coupled to the base of the 2nd low IF amplifier.

2ND LO IF AMPLIFIER AND LIMITERS (A348)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A348-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (A348-Q2, -Q3 and -Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

DISCRIMINATOR (A348)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CR1 and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network C16 and R23.

AUDIO - NOISE AMPLIFIER (A348)

The discriminator output is coupled through a low-pass filter (C16, C18, R21 and R22) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator output. Q5 operates as a emitter-follower to match the discriminator impedance to the VOLUME control, SQUELCH control, and Channel Guard input. The stage also provides power gain.

AUDIO AMPLIFIERS (A348)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-emphasis network consists of C22, C23, R30 and R31.

Audio driver Q7 follows the audio amplifier. The audio output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q341 and Q342 operate as a push-pull, class AB audio PA stage. The PA output is coupled through audio transformer T341 to the loudspeaker. The yellow and white tertiary windings of T341 supply balanced feedback to the collector of Q7. The feedback winding minimizes distortion and prevents the pick-up of external electrical noise.

The PA stage provides a 5-watt output at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohms at the Control Unit). Base bias for the PA stage and the elimination of cross-over distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

— NOTE —

Do not adjust bias adjust potentiometer R43 unless PA transistors Q341 and Q342 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the Test Procedure.

SQUELCH (A348)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C30, C31 and R45, as well as C34 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off.

When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a signal (unsquelches), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker. A network composed of C38, CR7 and R62 slows down the switching action of Q10, preventing an obnoxious "thump" from being heard in the speaker.

Resistor R53 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced ty 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R53 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit. When the receiver squelches, audio driver Q7 turns off and its emitter potential drops to zero. This reduces the DC feedback through R53 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the ± 10 volts from J19. This turns off DC amplifier Q9 and turns on Q10, muting the receiver.

CHANNEL GUARD

Channel Guard Board Model 4EK16A10 is a fully transistorized encoder-decoder for use with MASTR Professional Series mobile and station combinations. The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

Encoder (A350)

Keying the transmitter removes the receiver mute +10 volts, and forward biases feedback control diode CR5, causing it to conduct. When conducting, the diode shunts R39, R35 and C19). This provides the necessary gain to the base of Q5 to permit oscillation.

The encoder tone is provided by selective amp-oscillator transistors Q5 and Q6 which oscillate at a frequency determined by the tone network. Negative feedback applied through the tone network to the base of Q5

prevents any gain in the stage except at the desired encode frequency.

Starting network R45, C21, C22 and CR6 provide an extremely fast starting time for the encoder tone. Keying the transmitter removes the receiver mute +10 volts, causing a pulse to be applied to the base of Q6 to quickly start the oscillator. Thermistor-resistor combination R32 and RT1 provides temperature compensation for the oscillator output. Limiter diodes CR3 and CR4 keep the tone amplitude constant.

Emitter-follower Q7 follows the oscillator circuit. The encoder tone is taken from the emitter of Q7 and applied to the transmitter.

Decoder (A350)

The decoder function is designed to eliminate all calls that are not tone coded for the Channel Guard Frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hookswitch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

Audio, tone and noise are taken from the emitter of the receiver audio-noise amplifier Q348-Q5 and is fed through A350-J1 to four tone amplifier and bandpass filter circuits. The filters remove the audio and high-frequency noise from the signal, and the tone amplifiers provide sufficient gain to insure clipping by limiter diodes CR1 and CR2. The clipping action eliminates variation in the squelch performance due to changes in tone deviation. The signal is then applied to selective amplifiers Q5 and Q6 which amplify only the tone determined by the tone network.

The output of the selective amplifier is applied through emitter-follower Q7 to the high gain, broad-band tone amplifiers Q8 and Q9. The output of Q9 is rectified by detector diodes CR7 and CR8, and the resulting negative DC voltage controls the squelch gate. Q8 is normally biased for low gain. When the tone is detected by CR7 and CR8, feedback is provided through R54 to quickly change the bias on Q8 for full gain. This ensures a more positive "unsquelching" action.

Squelch gate diode CR9 is normally forward biased by a positive DC voltage (approximately 1.5 volts) fed through R58. The forward bias causes CR9 to conduct, feeding a DC voltage to the base of DC

amplifier A348-Q10 in the receiver. This removes the bias on the receiver audio stages and holds them off.

When the proper tone is applied to the decoder, the negative DC voltage from the detector diodes back-biases squelch gate diode CR9 and cuts off the positive bias to the receiver DC amplifier A348-Q10. However, the receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

Placing the CHANNEL GUARD - OFF switch in the OFF position (or removing the microphone from its hookswitch) removes the ground to the base of the decoder DC switch (Q10), causing it to conduct. This back-biases squelch control diode CR9 and cuts off the positive bias to the receiver DC amplifier (A348-Q10). The receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

A tone rejection filter connected in parallel with A348-J12 (in the receiver) bypasses any incoming tone to ground. This attenuates the tone level reaching the receiver audio circuits. The filter is composed of C26, C27, C28, C29, L1 and R59.

An optional tone reject filter (A402) that is identical to the filter described above is available for use in two-way radios with transmitter Channel Guard only.

MAINTENANCE

DISASSEMBLY

To service the receiver from the top--

- Pull locking handle down and pull radio about one inch out of mounting frame.
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

- Pull locking handle down. Pull radio out of mounting frame.
- Remove screws in bottom cover. Pry up cover at back of receiver.
- 3. Slide cover back and lift off.

To remove the receiver from the system frame-- $\,$

- Loosen the two Phillips-head retaining screws in from casting (see Figure 2), and pull casting away from system frame.
- Remove the four screws in the back cover.

- 3. Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the

20-pin connector from the front of the receiver, and slide the unit out of the system frame.

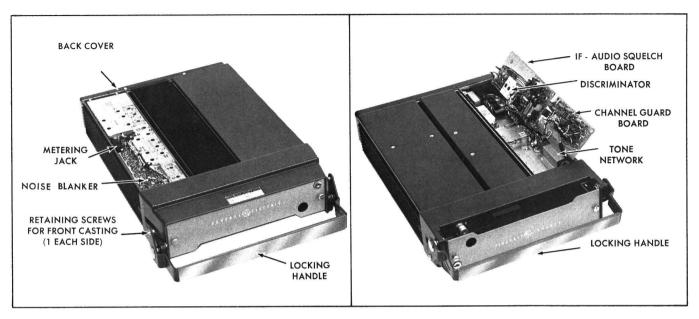


Figure 2 - Removing Top Cover

Figure 3 - Removing Bottom Cover

FRONT END ALIGNMENT

EQUIPMENT REQUIRED

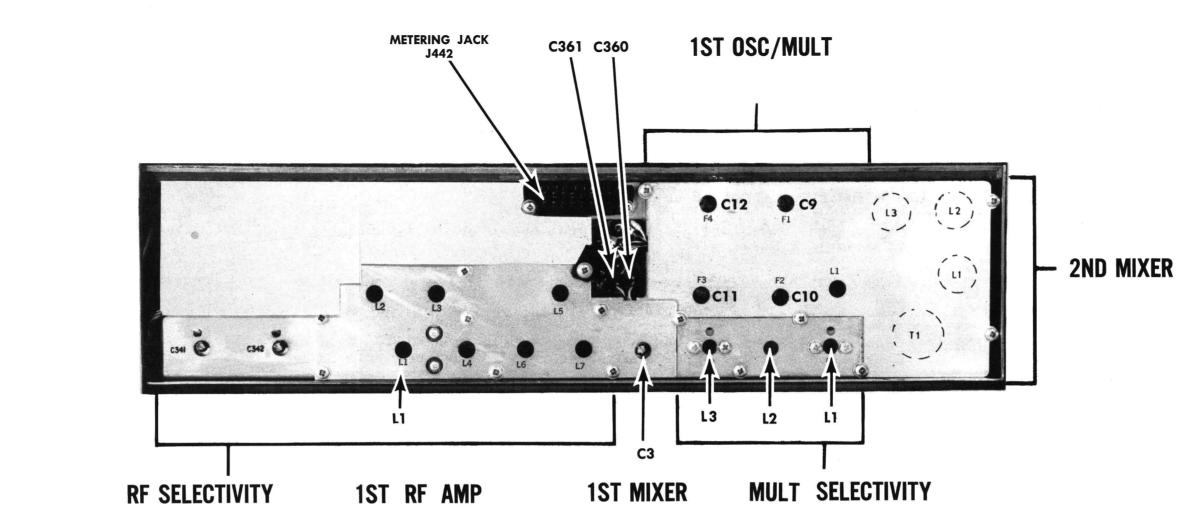
- 1. GE Test Set Models 4EX3A10, 4EX8K10, 11 (or 20,000 ohms-per-volt Multimeter with a 1-volt scale).
- A 455 kHz and 25-50 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

PRILIMINARY CHECKS AND ADJUSTMENTS

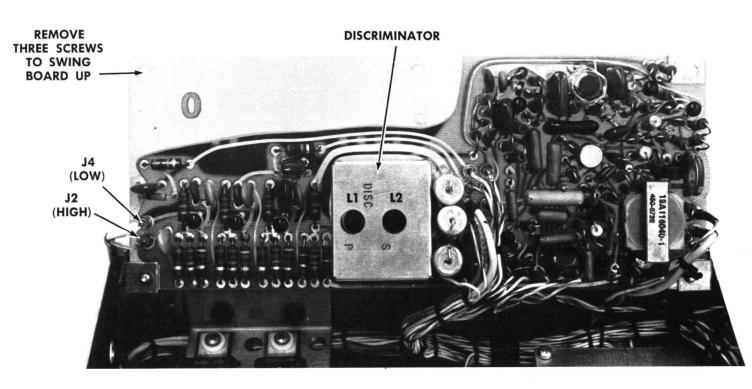
- Connect Test Set to Receiver Centralized Metering Jack J442 and set meter sensitivity switch to the TEST 1 position (or 1-volt position on 4EX8K10, 11).
- With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 3. If using Multimeter, connect the positive lead to J442-16 (Ground).
- 4. Disable Channel Guard.

ALIGNMENT PROCEDURE

	METERI	NG POSITION			
	GE Test	Multimeter		METER	
rep	Set	- at J442	TUNING CONTROL	READING	PROCEDURE
			OSCILLATOR/MUI	TIPLIER	
l.	D (MULT-1)	Pin 4	L4 (on 1st OSC/MULT) and L1, L2 (on MULT SELECTIVITY)	See Pro- cedure	Tune L4 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Then tune L2 for minimum meter reading. Change voltage scale if necessary. Repeat this step
			RF AMPLIFIER & S	SELECTIVITY	
2.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L7. Adjust the signal generator for discriminator zero.
3.	B (2nd IF Amp)	Pin 2	L1 (1st RF Amp), L6, L7, C341 and C342 (RF SELEC- TIVITY)	Maximum	Apply an on-frequency signal to the antenna jack, keeping below saturation. Tune L1, L6, L7, C341, and C342 for maximum meter reading.
1.	"	"	L4 (1st OSC/MULT) L1, L2 and L3 (MULT SELECTIVITY)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L4 on 1st OSC/MULT and L1, L2 and L3 on MULT SELECTIVITY for maximum meter reading.
			FREQUENCY ADJ	USTMENT	
•	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multi- frequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading In multi-frequency units, tune C10, C11 or C12 as required.
					For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment i outside the temperature rang of 50° to 90° F.



IF-AUDIO & SQUELCH



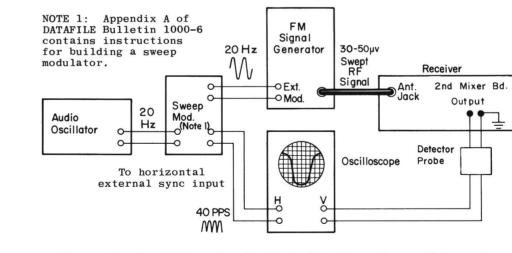


Figure 4 - Test Setup for 20-Hz Double-Trace Sweep Alignment

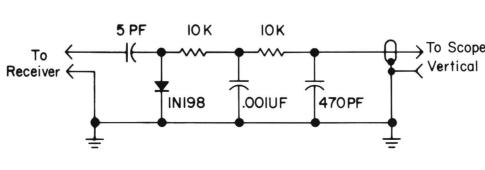


Figure 5 - Detector Probe for Sweep Alignment

COMPLETE RECEIVER ALIGNMENT

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3A10, 4EX8K10, 11 (or 20,000 ohms-per-volt Multimeter with a 1-volt scale).
- 2. A 455-kHz signal source (GE Test Set Model 4EX7A10) and 25-50 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output prove.

PRELIMINARY CHECKS AND ADJUSTMENTS

- Connect Test Set to Receiver Centralized Metering Jack J442, and set meter sensitivity switch to the TEST 1 position (or 1-volt position on 4EX8K10, 11).
- Set crystal trimmer C9 to mid-capacity. In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required. Where the maximum frequency spacing is less than 100 kHz, align the unit on channel F1. If the frequency spacing is greater than 100 kHz, align the receiver on the center frequency.
- 3. With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 4. If using Multimeter, connect the positive lead to J442-16 (Ground).
- 5. Disable the Channel Guard.

ALIGNMENT PROCEDURE

	METERING 1	POSITION			
STEP	GE Test Set	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
			DISC	RIMINATOR &	OSCILLATOR
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero	Remove three screws and swing open the IF-AUDIO & SQUELCH board. Adjust L1 (disc primary) 1/2 turn counterclockwise from the bottom coil. Next, apply a 455-kHz signal to J2 and J4 and adjust L2 (dis secondary) for zero meter reading.
2.	A (DISC)	Pin 10		See Pro- cedure	Alternately apply a 450-kHz and 460-kHz signal and check for reading of at least 0.3 volt, but not more than 0.5 volt on GE Test Set. By readings must be within .05 volt. Do not attempt to balance readings closer than .05 volt.
3.	D (MULT-1)	Pin 4	L4 (on 1st OSC/MULT) and L1, L2 & L3 (on MULT SELECTIVITY)	See Pro- cedure	Tune L4 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Tune L2 for minimum meter reading. Change voltage scale necessary. Then tune L3 for maximum meter reading. Repeat step 3.
		•	RF A	MPLIFIER &	SELECTIVITY
4.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L7. Adjust the signal generator for discriminator zero.
5.	B (2nd IF	Pin 2	L7 and L6 (RF SELECTIVITY)	Maximum	Apply an on-frequency signal and tune for maximum meter reading as shown below, keeping signal below saturation.
	AMP)				Apply Signal Generator Probe to:
					L6 L7
					L1 L6
6.	"	"	C341, C342 and L1 (1st RF Amp)	Maximum	Apply an on-frequency signal to the antenna jack. Tune C341, C342 and L1 for maximum meter reading, keeping signal below saturation.
7.	"	"	L1 (1st RF Amp) L6, L7, C341, and C342 (RF SELECTIVITY)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L1, L6, L7, C341 and C342 for maximum meter reading.
8.	,,	"	L3 (MULT SELECTIVITY)	Maximum	Apply on-frequency signal as above, keeping below saturation. Tun L2 & L3 (on MULT SELECTIVITY) for maximum meter reading.
	-			OND 117	XER & LO IF

The 1st and 2nd mixer, and low IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary, use the procedure outlined in STEPS 9, 10, and 11. CZ (on 1st mixer) does not peak, but provides impedance matching for the crystal filter input and should only be tuned when observing IF trace on oscilloscope.

Refer to DATAFILE BULLETIN 1000-6 (IF Alignment of Two-Way Radio FM Receivers) for helpful suggestions on how to determine when IF Alignment is required.

9.	B (2nd IF AMP)	Pin 2	A 347-L3, L2, L1, T1 (2nd Mixer)	Maximum	Apply on-frequency, unmodulated signal and tune A347-L3, L2, L1, and T1 for maximum meter reading, keeping signal below saturation.
10.			A347-L3, L2, L1, T1 (2nd Mixer)		Connect scope, signal generator, and detector as shown in Figure 4, Set signal generator level for 30-50 µv and modulate with 10 kHz at 20 Hz. With detector at the collector of A347-Q3 (2nd mixer board output), tune L3, L2, L1, T1 (2nd Mixer) and C3 (1st Mixer) for double trace as shown on scope pattern.
11.	A (DISC)	Pin 10		See Pro- cedure	Check to see that discriminator idling voltage is within ±.05 volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between ±7 and 9 kHz.
			FI	REQUENCY AD	JUSTMENT
12.	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multi-frequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.

_____ NOTE ____

ALIGNMENT PROCEDURE

25-50 MHZ, MASTR RECEIVER MODELS 4ER39C10-27 For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.

Issue 3

LBI-3924

LBI-3924

SIGNAL GENERATOR

DEVIATION

CONTROL

ANTENNA

TEST PROCEDURES

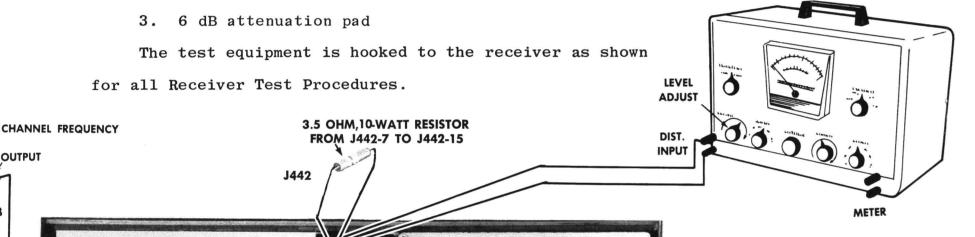
These Test Procedures are designed to help you to service a receiver that is operating---but not properly. The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized.

Once the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

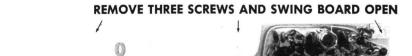
TEST EQUIPMENT REQUIRED

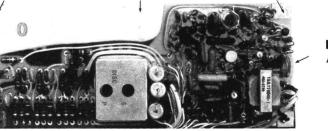
for test hookup shown:

- 1. Distortion Analyzer similar to: Heath #1M-12
- 2. Signal Generator similar to: Measurements #M-560

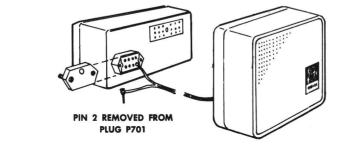


COMPONENT TOP VIEW





PA BIAS
ADJUST
R43



DISTORTION ANALYZER

IF-AUDIO & SQUELCH BOARD (COMPONENT VIEW)

STEP 1

AUDIO POWER OUTPUT AND DISTORTION TEST PROCEDURE

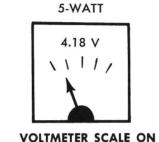
Measure Audio Power Output as follows:

- A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz ±3.3 kHz deviation to the antenna jack J441.
- B. With Five-Watt Speaker:

Disconnect speaker lead pin from J701-2 (on rear of Control Unit).

Connect a 3.5-ohm load resistor from J442-15 to J442-7. Connect the Distortion Analyzer input across the resistor as shown.

R



DISTORTION ANALYZER

With Handset:

Lift the handset off of the hookswitch. Connect the Distortion Analyzer input from J442-15 to J442-7.

- C. Set the VOLUME control for five-watt output (4.18 VRMS).
- D. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%.

SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than five watts, make the following checks:

- E. Battery and regulator voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- F. P.A. Bias Adjust (R43) -- Turn the SQUELCH control fully counterclockwise. Then connect a milliammeter in series with the +12-volt lead at P443-11. With no signal in, adjust R43 for a reading of approximately 20 milliamps. This adjustment should not be necessary unless an output transistor has been replaced.
- G. Audio Gain (Refer to Receiver Troubleshooting Procedure).
- H. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

STEP 2

USABLE SENSITIVITY (12 dB SINAD) TEST PROCEDURE

Measure sensitivity of the receiver modulated at the standard test modulation as follows:

- A. Be sure Test Step 1 checks out properly.
- B. Reduce the Signal Generator output from setting in Test Step 1A.
- C. Adjust Distortion Analyzer LEVEL control for a +2 dB reading.
- D. Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 2B and 2C until difference in reading is 12 dB (+2 dB to -10 dB).
- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is "usable" sensitivity level. Reading should be less than 0.25 microvolts with audio output at least 2.5 watts (2.9 volts RMS across the 3.5-ohm receiver load).

SERVICE CHECK

If the sensitivity level is more than 0.25 microvolts, make the following checks:

- F. Alignment of RF stages (Refer to RF Alignment in Receiver Alignment on reverse side of page).
- G. Gain measurements as shown on the Receiver Troubleshooting Procedure.

STEP 3

MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH) TEST PROCEDURE

- A. Be sure Test Steps 1 and 2 check out properly.
- B. Set Signal Generator output for twice the microvolt reading obtained in Test Step 2D.
- C. Increase Signal Generator frequency deviation.
- D. Adjust LEVEL Control for +2 dB.



DISTORTION ANALYZER

E. Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 3C, 3D and 3E until difference between readings becomes 12 dB (from +2 dB to -10 dB).



LEVEL

F. Deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ± 7 kHz (but less than ± 9 kHz).

SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

STEP 1 - QUICK CHECKS

TEST SET CHECKS

These checks are typical voltage readings measured with GE Test Set Model 4EX3A10 in the Test 1 position, or Model 4EX8K10 or 11 in the 1-volt position.

Metering Position	Reading With No Signal In	Reading with 1 Micro- volt Unmodulated
A (Disc Idling)	Less then ±.05 VDC	
B (2nd IF)	.03 VDC	0.2 VDC
C (1st Lim)	0.5 VDC	0.8 VDC
D (Mult-1)	0.6 VDC	
J (Reg. +10 volts)	+10 VDC	

SYMPTOM CHECKS

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	• Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.
NO REGULATED 10-VOLTS	• Check the 12-volt supply. Then check regulator circuit. (See Troubleshooting Procedure for Power Supply).
LOW 1ST LIM READING	• Check supply voltages and then check oscillator reading at J442-4 & 5 as shown in STEP 2A.
	• Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.
LOW OSCILLATOR/MULTI- PLIER READINGS	• Check alignment of Oscillator, (Refer to Front End Alignment Procedure).
	• Check voltage readings of 1st Oscillator/Multi- plier Q1/Q2.
	• Check crystal Yl.
LOW RECEIVER SENSITIV- ITY	• Check Front End Alignment. (Refer to Receiver Alignment Procedure).
	• Check antenna connections, cable and relay.
	• Check 1st and 2nd Oscillator injection voltage.
	• Check voltage readings of 1st Mixer, HI IF Amp and 2nd Mixer.
	• Make SIMPLIFIED GAIN CHECKS (STEP 2A).
LOW AUDIO	• Check Audio PA (Q341 & Q342) voltage readings on schematic diagram.
	 Make simplified gain and waveform checks of audio and squelch stages. (Steps 2A and 2B).
	• Make unsquelched voltage readings in Audio section. (Refer to Receiver Schematic Diagram).
	• Check voltage readings on Channel Guard board.
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	• Set PA bias adjust R43 as specified under Service Checks in STEP 1 of TEST PROCEDURES.
IMPROPER SQUELCH OPERA- TION	 Check voltage readings of Squelch circuit. (Refer to Receiver Schematic Diagram).
	 Make gain and waveform checks of audio and squelch stages. (Steps 2A and 2B).
DISTORTION IDLING TOO FAR OFF ZERO	See if discriminator zero is in center of IF bandpass.

STEP 3-VOLTAGE RATIO READINGS -

EQUIPMENT REQUIRED:

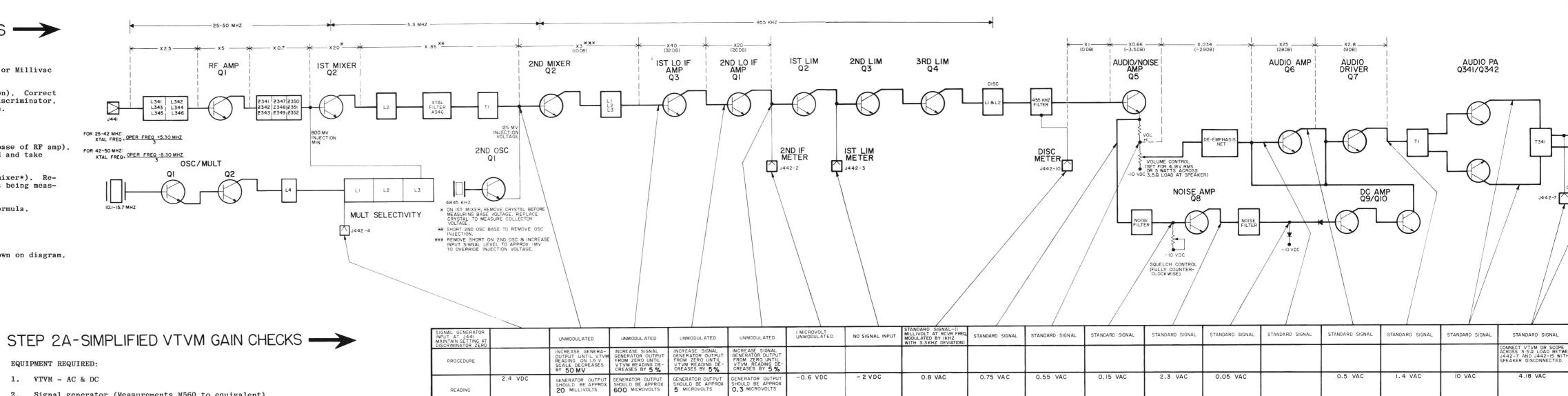
- 1. RF Voltmeter (similar to Boonton Model 91-CA or Millivac Type MV-18 C.
- 2. Signal on receiver frequency (below saturation). Correct frequency can be determined by zeroing the discriminator. Use 1,000 hertz signal with 3.3 kHz deviation.

PROCEDURE:

- 1. Apply probe to input of stage (for example, base of RF amp). Peak resonant circuit of stage being measured and take voltage reading (E1).
- Move probe to input of following stage (1st mixer*). Repeak first resonant circuit then peak circuit being measured and take reading (E2).
- 3. Convert readings by means of the following formula.

Voltage Ratio =
$$\frac{E_2}{E_1}$$

4. Check results with typical voltage ratios shown on diagram.



(RC-1687A)

EQUIPMENT REQUIRED:

1. VTVM - AC & DC

2. Signal generator (Measurements M560 to equivalent).

PRELIMINARY STEPS:

- Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- 4. Connect VTVM between system negative and points indicated by arrow.

CTED OD ALIDIC	0 0 001111 011	\A\A\\/EEODMC	
STEP 2B-AUDIC	U OK SQUELUM	MAVELOUINS	

EQUIPMENT REQUIRED:

Oscilloscope.

2. Signal generator (measurements M560 to equivalent).

PRELIMINARY STEPS:

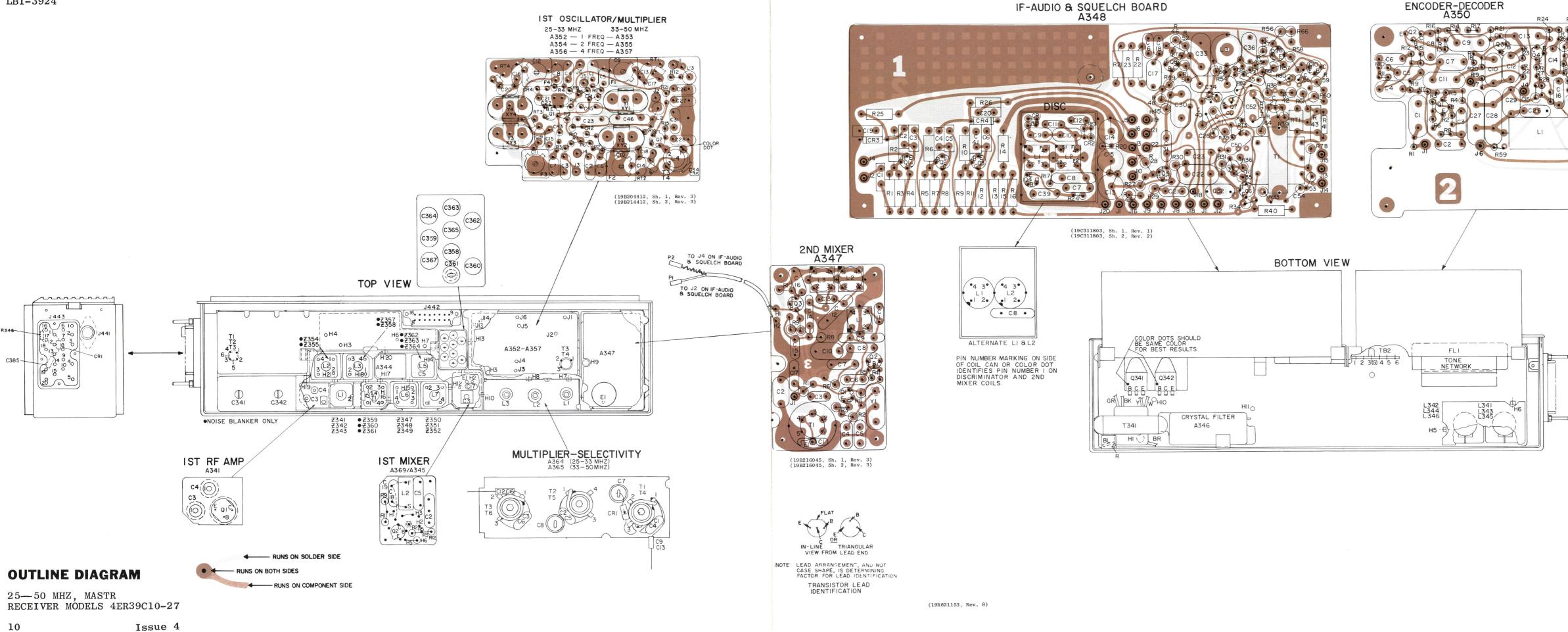
- 1. Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- 4. Connect oscilloscope between system negative and points indicated by arrow.

COPE SETTING	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	O.5 MS/DIV	0.5 MS/DIV	0.5 MS/DIV	O.5 MS/DIV	O.5 MS/DIV	O.5 MS/DIV
OOI E SETTINO	I VOLT/DIV	I VOLT/DIV	I VOLT/DIV	2 VOLTS/DIV	0.5 VOLTS/DIV	50 MILLIVOLTS/DIV	I VOLT/DIV	2 VOLTS/DIV	IO VOLTS/DIV	5 VOLTS/DIV
	2 V P-P	1.4 V P-P	IV P-P (NOISE)	5.7 V P-P (NOISE)	3 V P-P (NOISE)	0.1 V P-P	1.9 V P-P	4 V P-P	30 V P-P	12 V P-P
STANDARD SIGNAL (I MILLIVOLT AT RECEIVER FREQ MODULATED BY IKHZ WITH 3.3 KHZ DEVIATION)					3-47-43-45-4C					
NOISE WAVE FORM (NO SIGNAL INPUT)	PRINTER				TOTAL STATE	Margaziki	Secret Market			

TROUBLESHOOTING PROCEDURE

25-50 MHZ, MASTR RECEIVER MODELS 4ER39C10-27

Issue 2



CHANNEL GUARD

(19C311794, Sh. 1, Rev. 2) (19C311794, Sh. 2, Rev. 2)

PARTS LIST

LBI-3914C

25-50 MHz RECEIVER

SYMBOL	GE PART NO.	DESCRIPTION
A341		RF AMPLIFIER ASSEMBLY 19B204772-G1
C1	5494481-P12	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim tRMC Type JF Discap.
C2	5494481-Pl4	Ceramic disc: .002 µf ±10%, 1000 VDCW; sim t
C3 and C4	5493392-P7	Ceramic, feed-thru: .001 µf +100% -0%, 500 sim to Allen-Bradley Type FASC.
		TRANSISTORS
Q1	19Al15342-P1	Silicon, NPN.
		RESISTORS
Rl	3R152-P123K	Composition: $12,000$ ohms $\pm 10\%$, $1/4$ w.
R2	3R152-P302J	Composition: 3000 ohms $\pm 5\%$, $1/4$ w.
R3	3R152-P102K	Composition: 1000 ohms $\pm 10\%$, $1/4$ w.
R4	3R 15 2-P3 91 K	Composition: 390 ohms ±10%, 1/4 w.
		SOCKETS
XQ1	5490277-P1	Transistor: 4 contacts rated at 1 amp at 400 VRMS; sim to Elco 3303.
345		FIRST MIXER ASSEMBLY 19B204430-G2
C2	5494481-P114	Ceramic disc: .002 µf ±10%, 1000 VDCW; sim t
СЗ	5491271-P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189-6-5.
C5	5494481-P114	Ceramic disc: .002 µf ±10%, 1000 VDCW; sim tRMC Type JF Discap.
C6	5494481-P12	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim tRMC Type JF Discap.
C18	5496218-P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef
		TERMINALS
El	4038104-P1	Lug.
L2	19 A1 21 08 2-G2	Toroidal coil.
		TRANSISTORS
Q2	19A115245-P1	Silicon, NPN.
		RESISTORS
R1	3R152-P563J	Composition: $56,000$ ohms $\pm 5\%$, $1/4$ w.
R2	3R 15 2-P8 22J	Composition: 8200 ohms ±5%, 1/4 w.
R3	3R 15 2-P202J	Composition: 2000 ohms ±5%, 1/4 w.
R5	3R152-P390J	Composition: 39 ohms $\pm 5\%$, $1/4$ w.
R9	3R152-P471K	Composition: 470 ohms ±10%, 1/4 w.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.

	CRYSTAL FILTER				
		R6	3R77-P332K	Composition: 3300 ohms ±10%, 1/2 w.	C27*
	19B204616-G3	R7	3R77-P123K	Composition: 12,000 ohms ±10%, 1/2 w.	
		R8	3R77-P622J	Composition: 6200 ohms ±5%, 1/2 w.	C28*
19B206692-G1	Bandpass.	R9	3R77-P302J	Composition: 3000 ohms ±5%, 1/2 w.	
		R10	3R77-P202J	Composition: 2000 ohms ±5%, 1/2 w.	C29*
3R152-P562K	Composition: 5600 ohms ±10%, 1/4 w.	R11	3R77-P201J	Composition: 200 ohms ±5%, 1/2 w.	C30
3R152-P103K	Composition: 10,000 ohms ±10%, 1/4 w.				C31
	SECOND MIXER	T1			C32
	19 B2 16 119 - G1 REV A	"		COIL ASSEMBLY 19B216120-G1	C33
					C34
		C1	19C301540-P261	Ceramic disc: 82 pf ±5%, 200 VDCW, temp coef	
	(Part of Tl).			-80 PPM.	C35
19B209243-P7	Polyester: 0.1 μf ±20%, 50 VDCW.		5491 798-P3	Tuning slug.	C36*
5494481-P112	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.				C37*
5490008-P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	Yl	19 Al 10 19 2- P3	Quartz: freq 4845 KHz ±100 Hz at 25°C, temp range -30°C to +75°C.	C37*
54 90 00 8-P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	A348		IF AUDIO AND SQUELCH 19D413129-G1	C38*
19B209243-P5	Polyester: 0.047 μf ±20%, 50 VDCW.				900
5496219-P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.	C1	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C39 C40*
19B209243-P7	Polyester: 0.1 µf ±20%, 50 VDCW.	C2	5496219-P717	Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef	1
5496219-P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.	сз	5494481-P111		C41
5496219-P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef	C4	5496219-P717	RMC Type JF Discap.	C42*
5496219-P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef			-750 PPM.	C43*
5496219-P471	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef	and C6	5494481-P111	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C49*
7491395-P109		C7	19B209243-P5	Polyester: 0.047 µf ±20%, 50 VDCW.	C50*
19B209243-P5	RMC Type JL.	C8	5496219-P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150.	C51*
19B209243-P1	Polyester: 0.01 µf ±20%, 50 VDCW. Added by Rev A.	C9 and C10	5490008-P37	Silver mica: 270 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C52*
	JACKS AND RECEPTACLES	C11	5496219-P656	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -470 PPM.	C53* and C54*
4033513-P4	Contact, electrical; sim to Bead Chain L93-3.	C12	5494481-P108	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C55*
100011101 00	INDUCTORS	C13	19A115680-P107	Electrolytic: 100 µf +150% -10%, 15 VDCW; sim to Mallory Type TT.	
190311181-03		Cl4 and Cl5	19A115680-P104	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.	CR1 and CR2
4029840-P2		C16	5494481-P112	Ceramic disc: .001 µf ±10%, 500 VDCW; sim to RMC Type JF Discap.	CR3 and
4029840-P1	Contact, electrical: sim to AMP 41854.	C17	19B209243-P7		CR4
İ		C18	5494481-P108	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to	CR5 and
104115000 70					CR6
	· · · · · · · · · · · · · · · · · · ·	and	19B209243-P5	Polyester: 0.047 μf ±20%, 50 VDCW.	CR7*
	'	1 1	10 2200 242 22	Polymeters 0 000 of toom 50 years	CR8*
		0217	19B209243-P3 19B209243-P1	Polyester: 0.022 µf ±20%, 50 VDCW. Earlier than REV A. Polyester: 0.01 µf ±20%, 50 VDCW.	
		C22	19 B2 09 24 3-P1 16	Polyester: 0.15 µf ±10%, 50 VDCW.	J1 thru
эк 77-Р103К	Composition: 10,000 ohms ±10%, 1/2 w.	C23	19B209243-P107	Polyester: 0.1 µf ±10%, 50 VDCW.	J22
20 77 PELO-	0	C24*	19B209243-P106	Polyester: .068 µf ±10%, 50 VDCW.	
			5400525 = -	Deleted by REV A.	Ll
3R152-P333K 3R152-P103J	Composition: 33,000 ohms ±10%, 1/4 w. Composition: 10,000 ohms ±5%, 1/4 w.			Sprague Type 150D.	L2 L3
		C26*	5496267-P28 19B209243-P14	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A. Polyester: 0.33 µf ±20%, 50 VDCW.	
	5490008-P95 5490008-P9 19B209243-P5 5496219-P369 19B209243-P7 5496219-P40 5496219-P40 5496219-P471 7491395-P109 19B209243-P5 19B209243-P1 4033513-P4 19C311181-G3 4029840-P2 4029840-P1 19A115245-P1 19A115245-P1 19A115123-P1 3R77-P103K 3R77-P512J 3R152-P333K	Ceramic disc: .001 µf f10%, 1000 VDCW; sim to RMC Type JF Discap. Silver mica: 220 pf f5%, 500 VDCW; sim to Electro Motive Type DM-15. Silver mica: 18 pf f5%, 500 VDCW; sim to Electro Motive Type DM-15. 19B209243-P5 Polyester: 0.047 µf f20%, 50 VDCW. Ceramic disc: 180 pf f5%, 500 VDCW, temp coef -150 PPM. Polyester: 0.1 µf f20%, 50 VDCW. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 220 pf f5%, 500 VDCW, temp coef oPPM. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 9 pf f0.25 pf, 500 VDCW, temp coef oPPM. Ceramic disc: 220 pf f5%, 500 VDCW, temp coef oPPM. Ceramic disc: 0.01 µf f10%, 500 VDCW, temp coef oPPM. Polyester: 0.047 µf f20%, 50 VDCW. Added by Rev A.	Ceramic disc: .001 \(\text{ \text{ pf biscap.}} \)	S494481-P112 Ceramic disc: 001 pf ±10%, 1000 VDCW; sin to Electro Motive Type JF Discap. Silver mica: 220 pf ±5%, 500 VDCW; sin to Electro Motive Type DM-15.	198408-P13

5496267-P2 5496267-P6 5496267-P229 5496267-P17 19B209243-P16	Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. Earlier than REV C: Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D. Tantalum: 0.68 µf ±10%, 35 VDCW; sim to Sprague Type 150D. Deleted by REV A.	Q1 thru
5496 267-P229 5496 267-P17 19B209243-P16	Sprague Type 150D. Earlier than REV C: Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague Type 150D. Tantalum: 0.68 µf ±10%, 35 VDCW; sim to	
5496267-P17 19B209243-P16	Tantalum: 0.68 µf ±10%, 35 VDCW; sim to	
19B209243-P16	opragae Type 100D, Derected by KEV A.	Q6 Q7
	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to	Q8
	Sprague Type 150D. Deleted by REV A. Polyester: 0.15 µf ±20%, 50 VDCW.	Q9
19B209243-P102	Polyester: 0.015 µf ±20%, 50 VDCW.	Q10
19B209243-P7	Polyester: 0.1 µf ±20%, 50 VDCW.	
19B209243-P17	Polyester: 0.22 µf ±20%, 50 VDCW.	R1
40 29 00 3-P2 07	Silver mica: 1830 pf ±2%, 500 VDCW; sim to Electro Motive Type DM-20.	R2
19 B2 09 24 3- P5	Polyester: 0.047 µf ±20%, 50 VDCW.	R3
19B209243-P17	Polyester: 0.22 µf ±20%, 50 VDCW.	R4
19B209243-P7	Earlier than REV C: Polyester: 0.1 µf ±20%, 50 VDCW.	R5
5496267-P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to	R6
5496267-P17	Sprague Type 150D. Earlier than REV A: Tantalum: 1.0 µf ±20%, 35 VDCW; sim to Sprague Type 150D.	R7 R8
5496267-P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to	R9
5496267-P14	Sprague Type 150D. Deleted by REV C. Earlier than REV A.	R10
5490207-P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.	R11
19B209243-P1	Polyester: 0.01 µf ±20%, 50 VDCW.	R12
5496267-P28	Tantalum: 0.47 µf ±20%, 35 VDCW; sim to Sprague Type 150D. Earlier than REV A:	R13
19B209243-P117	Polyester: 0.22 µf ±10%, 50 VDCW.	R14
5490008-P129	Silver mica: 120 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	R15
19B209243-P4	Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by REV A.	R16 R17
5496267-P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Deleted by REV A.	R18 and
5496 26 7-P9	Tantalum: 3.3 µf ±15%, VDCW; sim to Sprague Type 150D. Added by REV A. Deleted by REV C.	R19 R20
19B209243-P7	Polyester: 0.1 µf ±20%, 50 VDCW. Added by REVA.	R21
5494481-P127	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV. A.	and R22
19B209243-P117	Polyester: 0.22 µf ±10%, 50 VDCW. Added by REV. A.	R23 R24
5496267-P213	Tantalum: 2.2 µf ±10%, 20 VDCW; sim to Sprague Type 150D. Added by REV A.	R25
5496267-P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. Added by REV C.	R26 R27 and
	·	R28
	DIODES AND RECTIFIERS	R29
19 A1 15 250-P1	Silicon.	R30
4038056-Pl	Germanium.	R31 R32*
19A115250-P1	Silicon.	R33*
	İ	R34
19 A1 15 250-P1	Silicon. Deleted by REV C.	R35
19A115250-P1	Silicon. Added by REV A. Deleted by REV C.	R36
İ	JACKS AND RECEPTACLES	R37*
4033513-P4	Contact, electrical: sim to Bead Chain L93-3.	R38*
		R39*
19C311181-G1	Coil.	
19C311181-G2	Coil. Includes tuning slug 4038368-Pl.	R40
19A1 271 34-G1	Choke. Includes tuning slug 7486872-P7.	

GE PART NO.

19Al15123-Pl

19A115300-P4

19A115123-P1

19 Al 15362-Pl

19Al15123-Pl

3R77-P102K

3R77-P153J

3R77-P823K

3R77-P472K

3R 77-P10 2K

3R77-P153J

3R 77-P823K

3R77-P472K

3R77-P102K

3R 77-P153J

3R 77-P823K

3R77-P472K

3R 77-P272K

3R 77-P103J

38.77-P333J

3R77-P181K

3R152-P471J

3R152-P513J

3R152-P472K

3R 77-P36 2J

3R77-P104K

3R152-P102J

3R77-P103K

3R.77-P753J

3R 77-P182J

3R77-P102J

3R77-P821J

3R77-P752J

3R77-P912J

38.77-P203J

3R77-P332K

3R77-P330K

3R77-P681J

3R 77-P822J

3R 77-P75 2J

3R 77-P622J

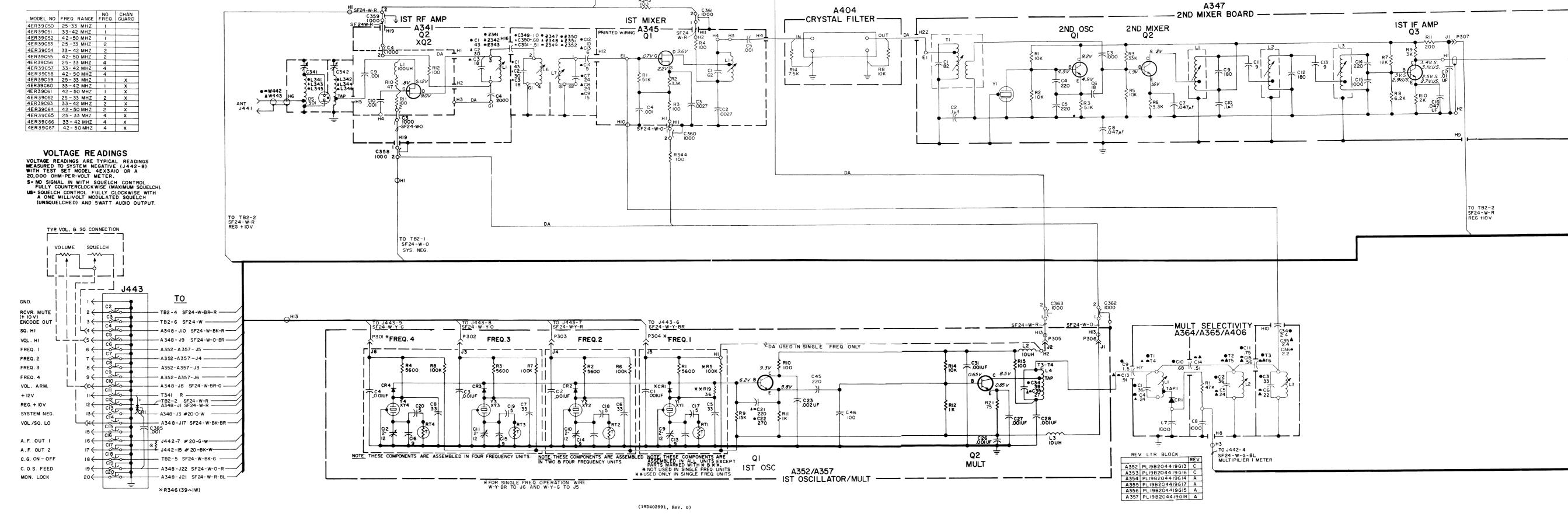
3R77-P820J

3R 77-P13 LJ

3R 77-P24 LJ

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
Silicon, NPN; sim to Type 2N2712.	R41*	3R152-P240J	Composition: 24 ohms ±5%, 1/2 w. Earlier than REV A:	T1
officon, new, sim to type anatia.	R42*	3R77-P300J 3R77-P200J	Composition: 30 ohms ±5%, 1/2 w. Composition: 20 ohms ±5%, 1/2 w.	
Silicon, NPN; sim to Type 2N3053.	842*	3R77-P160J	Earlier than REV A: Composition: 16 ohms ±5%, 1/2 w.	A350
Silicon, NPN; sim to Type 2N2712.	R43	19B209358-P101	Variable, carbon film: approx 25 to 250 ohms	1000
Silicon, NPN; sim to Type 2N2925.	R44	19B209022-P101	$\pm 10\%$, 0.2 w; sim to CTS Type X-201. Wirewound: .27 ohms $\pm 10\%$, 2 w; sim to IRC	
Silicon, NPN; sim to Type 2N2712.		135203022-2101	Type BWH.	C1*
RESISTORS	R45	3R.77-P123J	Composition: 12,000 ohms ±5%, 1/2 w.	C2*
Composition: 1000 ohms ±10%, 1/2 w.	R46 R48*	3R 77-P913J 19A116278-P249	Composition: 91,000 ohms ±5%, 1/2 w. Metal film: 3160 ohms ±2%, 1/2 w.	and C3*
Composition: 15,000 ohms ±5%, 1/2 w.		3R.77-P302J	Earlier than REV B: Composition: 3000 ohms ±5%, 1/2 w.	C4*
Composition: 82,000 ohms ±10%, 1/2 w. Composition: 4700 ohms ±10%, 1/2 w.		3R77-P332J	Earlier than REV A: Composition: 3300 ohms ±5%, 1/2 w.	C5*
Composition: 1000 ohms ±10%, 1/2 w.	R49	3R77-P103J	Composition: 10,000 ohms $\pm 5\%$, 1/2 w.	C6*
Composition: 15,000 ohms ±5%, 1/2 w.	R50	3R77-P222J	Composition: 2200 ohms ±5%, 1/2 w.	C7*
Composition: 82,000 ohms ±10%, 1/2 w.	R51	3R77-P103J	Composition: 10,000 ohms ±5%, 1/2 w.	C9*
Composition: 4700 ohms ±10%, 1/2 w.	R52 R53*	3R.77-P682J 3R.77-P303J	Composition: 6800 ohms ±5%, 1/2 w.	C10*
Composition: 1000 ohms ±10%, 1/2 w.	R55+	3R77-P473J	Composition: 30,000 ohms ±5%, 1/2 w. Earlier than REV C: Composition: 47,000 ohms ±5%, 1/2 w.	C11*
Composition: 15,000 ohms ±5%, 1/2 w. Composition: 82,000 ohms ±10%, 1/2 w.		3R.77-P303J	Earlier than REV A: Composition: 30,000 ohms ±5%, 1/2 w.	C12*
Composition: 4700 ohms ±10%, 1/2 w.	R54	3R77-P822J	Composition: 8200 ohms ±5%, 1/2 w.	C13*
Composition: 2700 ohms ±10%, 1/2 w.	R55	38.77-P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C14*
Composition: 10,000 ohms ±5%, 1/2 w.	R56	3R 77-P 22 4J	Composition: 0.22 megohms $\pm 5\%$, $1/2$ w.	1 (15
Composition: 33,000 ohms ±5%, 1/2 w.	R57	3R77-P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C16*
Composition: 180 ohms ±10%, 1/2 w.	R58 R59	3R 77-P181K 3R 77-P393K	Composition: 180 ohms ±10%, 1/2 w. Composition: 39,000 ohms ±10%, 1/2 w.	C17
Composition: 470 ohms ±5%, 1/4 w.	R60	3R 77-P393K	Composition: 10,000 ohms ±10%, 1/2 w.	C18
Composition: 51,000 ohms ±5%, 1/4 w.	and R61		,	C19*
Composition: 4700 ohms ±10%, 1/4 w.	R62*	3R77-P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C20
Composition: 3600 ohms ±5%, 1/2 w.		3R 77-P22 3K	Earlier than REV A: Deleted by REV C. Composition: 22,000 ohms $\pm 10\%$, $1/2$ w.	C21
	R63*	3R77-P432J	Composition: 4300 ohms ±5%, 1/2 w. Deleted by REV A.	021
Composition: 0.1 megohm ±10%, 1/2 w.	R64*	3R77-P120J	Composition: 12 ohms ±5%, 1/2 w. Earlier than REV C:	C22
Composition: 1000 ohms ±5%, 1/4 w.		3R77-P180J	Composition: 18 ohms ±5%, 1/2 w.	C23
Composition: 10,000 ohms ±10%, 1/2 w.	R65*	3R77-P154K	Composition: 0.15 megohm ±10%, 1/2 w. Deleted by REV A.	C24
Composition: 75,000 ohms ±5%, 1/2 w.	R66	3R 77-P472K	Composition: 4700 ohms ±10%, 1/2 w.	
, , ,	R75*	3R 77-P473J	Composition: $47,000$ ohms $\pm 5\%$, $1/2$ w. Added by REV A. Deleted by REV C.	C25
Composition: 1800 ohms ±5%, 1/2 w.	R76*	3R152-P912J	Composition: 9100 ohms ±5%, 1/4 w.	C26*
Composition: 1000 ohms ±5%, 1/2 w.	200	00150 D1501	Added by REV A. Deleted by REV C.	C27* and
Composition: 820 ohms ±5%, 1/2 w.	R77*	3R152-P153J 3R152-P652J	Composition: 15,000 ohms ±5%, 1/4 w. Earlier than REV C: Composition: 5600 ohms ±5%, 1/4 w.	C28*
Composition: 7500 ohms ±5%, 1/2 w. Deleted by REV A.			Added by REV A.	229-
Composition: 9100 ohms $\pm 5\%$, $1/2$ w. Earlier than REV A.	R78*	3R 77-P100J	Composition: 10 ohms ±5%, 1/2 w. Added by REV A.	C30
Composition: 20,000 ohms ±5%, 1/2 w.	R79*	3R 15 2-P393J	Composition: 39,000 ohms $\pm 5\%$, $1/4$ w. Added by REV A.	
Composition: 3300 ohms ±10%, 1/2 w.	R80*	3R152-P432J	Composition: 4300 ohms ±5%, 1/4 w. Added by	
Composition: 33 ohms ±10%, 1/2 w. Composition: 680 ohms ±5%, 1/2 w.		m150 n450	REV C.	CR1 and
Composition: 8200 ohms ±5%, 1/2 w.	R81*	3R152-P472J	Composition: 4700 ohms ±5%, 1/4 w. Added by REV C.	CR2
Deleted by REV A.	R82*	3R77-P273J	Composition: 27,000 ohms ±5%, 1/2 w. Added by REV C.	CR3 and CR4
Composition: 7500 ohms ±5%, 1/2 w. Earlier than REV A. Composition: 6200 ohms ±5%, 1/2 w.			MUDD MY SWAD S	CR5
Composition: 8200 ohms ±5%, 1/2 w.	RT1	5490828-P41	THERMISTORS Thermistor: 30 ohms ±10%, color code black,	CR6
Earlier than REV A. Composition: 130 ohms ±5%, 1/2 w.			white; sim to Globar Type Bl2llH-4.	CR7 thru
Composition: 240 ohms ±5%, 1/2 w.	RT2	5490828- P 9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8.	CR9
	RT3*	5490828-P9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H8. Added by REV. A.	
			or dropping type country indicate by mark it.	
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	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
			TRANSFORMERS			
	Tl	19A116040-P1	Audio: Pri: 19.3 ohms ±10% DC res, Sec: 23.5 ohms ±10% DC res.	FL1		TONE FREQUENCY NETWORK 19B205280
	A350		ENCODER/DECODER 4EK16Al0 19C3ll797-G1 REV C		19B205280-G1 19B205280-G2 19B205280-G3 19B205280-G4 19B205280-G5	71.9 Hz 77.0 Hz 82.5 Hz 88.5 Hz 94.8 Hz
					19B205280-G6 19B205280-G7 19B205280-G8	100.0 Hz 103.5 Hz 107.2 Hz
-	C1*	19A116080-P9	Polyester: 0.22 µf ±20%, 50 VDCW.		19B205280-G9 19B205280-G10	110.9 Hz 114.8 Hz
	C2* and C3*	19A116080-P205	Polyester: 0.047 μf ±5%, 50 VDCW.		19 B205 280 - G11 19 B205 280 - G1 2 19 B205 280 - G1 3 19 B205 280 - G1 4	118.8 Hz 123.0 Hz 127.3 Hz 131.8 Hz
-	C4*	19 A1 16 080-P207	Polyester: 0.1 µf ±5%, 50 VDCW.		19B205280-G15 19B205280-G16	136.5 Hz 141.3 Hz
	C5*	19A116080-P7	Polyester: 0.1 µf ±20%, 50 VDCW.		19B205280-G17 19B205280-G18	146.2 Hz 151.4 Hz
-	C6*	19 A1 16080-P205	Polyester: 0.047 µf ±5%, 50 VDCW.		19B205280-G19 19B205280-G20	156.7 Hz 162.2 Hz
	C7*	19A116080-P207	Polyester: 0.1 µf ±5%, 50 VDCW.		19B205280-G21 19B205280-G22 19B205280-G23	167.9 Hz 173.8 Hz 179.9 Hz
-	C9*	19A116080-P205 19A116080-P9	Polyester: 0.047 µf ±5%, 50 VDCW. Polyester: 0.22 µf ±20%, 50 VDCW.		19B205280-G24 19B205280-G25	186.2 Hz 192.8 Hz
	C10*	19A116080-P207	Polyester: 0.1 µf ±5%, 50 VDCW.		19B205280-G26	203.5 Hz
ı	C11*	19A116080-P109	Polyester: 0.22 µf ±10%, 250 VDCW.			
	C12*	19A116080-P207	Polyester: 0.1 µf ±5%, 50 VDCW.	J1 thru	4033513-P4	Contact, electrical sim to Bead Chain L93-3.
	C13*	19A116080-P9	Polyester: 0.22 µf ±20%, 50 VDCW.	J8		
	C14*	19A116080-P7	Polyester: 0.1 µf ±20%, 50 VDCW.			INDUCTORS
	C15	5496267-P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	L1	19A115690-P1	Coil, RF: 880 MH ±5%, sim to Artted AC5672.
	C16*	19A116080-P5	Polyester: 0.047 µf ±20%, 50 VDCW.	Q1	19Al15123-P1	
	CIT	5496267-P417	Tantalum: 1.0 µf ±5%, 35 VDCW; sim to Sprague Type 150D.	Q2	19A115362-P1	Silicon, NPN; sim to Type 2N2925.
	C18	54 96 26 7-P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	Q3 and Q4	19A115123-P1	Silicon, NPN; sim to Type 2N2712.
	C19*	19A116080-P109	Polyester: 0.22 µf ±10%, 50 VDCW.	Q5	19A115362-P1	Silicon, NPN; sim to Type 2N2925.
	C20	5494481~P111 5496267~P9	Ceramic disc: .001 µf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Tantalum: 3.3 µf ±20%, 15 VDCW; sim to	thru Q8 Q9	19A115123-P1	
	C22	5496267-P17	Sprague Type 150D. Tantalum: 1.0 µf ±20%, 35 VDCW; sim to	and Q10	19/11/12/3-71	Silicon, NPN; sim to Type 2N2712.
1			Sprague Type 150D.			
- 1	C23	5496267-P13	Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D.	R1	3R152-P682K	Composition: 6800 ohms ±10%, 1/4 w.
	C24	5496267-Pl	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	R2	3R152-P683J	Composition: 68,000 ohms ±5%, 1/4 w.
-	C25	5496267-P18	Tantalum: 6.8 μf ±20%, 35 VDCW; sim to	R3	3R 15 2-P8 22J	Composition: 8200 ohms ±5%, 1/4 w.
-			Sprague Type 150D.	R4	3R152-P152J	Composition: 1500 ohms ±5%, 1/4 w.
ı	C26*	19A116080-P206	Polyester: 0.068 μf ±5%, 50 VDCW.	R5	3R152-P682K	Composition: 6800 ohms ±10%, 1/4 w.
	C27* and	19A116080-P210	Polyester: 0.33 μf ±5%, 50 VDCW.	R6 R7	3R152-P201J 3R152-P113J	Composition: 200 ohms ±5%, 1/4 w. Composition: 11,000 ohms ±5%, 1/4 w.
	C28* C29*	19A116080-P205	Polyester: 0.047 µf ±5%, 50 VDCW.	R8*	3R 15 2-P56 2J	Composition: 5600 ohms ±5%, 1/4 w.
	025	19B209243-P107	Earlier than REV C: Polyester: 0.1 µf ±10%, 50 VDCW.		3R152-P622J	Earlier than REV B: Composition: 6200 ohms ±5%, 1/4 w.
-	C30	5496267-P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to		3R152-P512J	Earlier than REV A: Composition: 5100 ohms ±5%, 1/4 w.
			Sprague Type 150D.	R9	3R152-P113J	Composition: 11,000 ohms ±5%, 1/4 w.
-			DIODES AND RECTIFIERS	R10	3R152-P512J	Composition: 5100 ohms ±5%, 1/4 w.
	CR1 and	19 Al 15 250-Pl	Silicon.	R11	3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.
	CR2			R12	3R152-P822J	Composition: 8200 ohms ±5%, 1/4 w.
-	CR3 and	5494922-P1	Silicon.	R13	3R152-P153J 3R152-P133J	Composition: 15,000 ohms ±5%, 1/4 w. Composition: 13,000 ohms ±5%, 1/4 w.
	CR4 CR5	19Al15250-Pl	Silicon.	R15	3R152-P510J	Composition: 51 ohms ±5%, 1/4 w.
	CR6	40 36 88 7-P3	Silicon, Zener.	R16	3R152-P153J	Composition: 15,000 ohms ±5%, 1/4 w.
	CR7	19 Al 15 250-Pl	Silicon.	R17	3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.
ow;	thru CR9			R18	3R152-P622J	Composition: 6200 ohms ±5%, 1/4 w.
ow;				R19	3R152-P123J	Composition: 12,000 ohms ±5%, 1/4 w.
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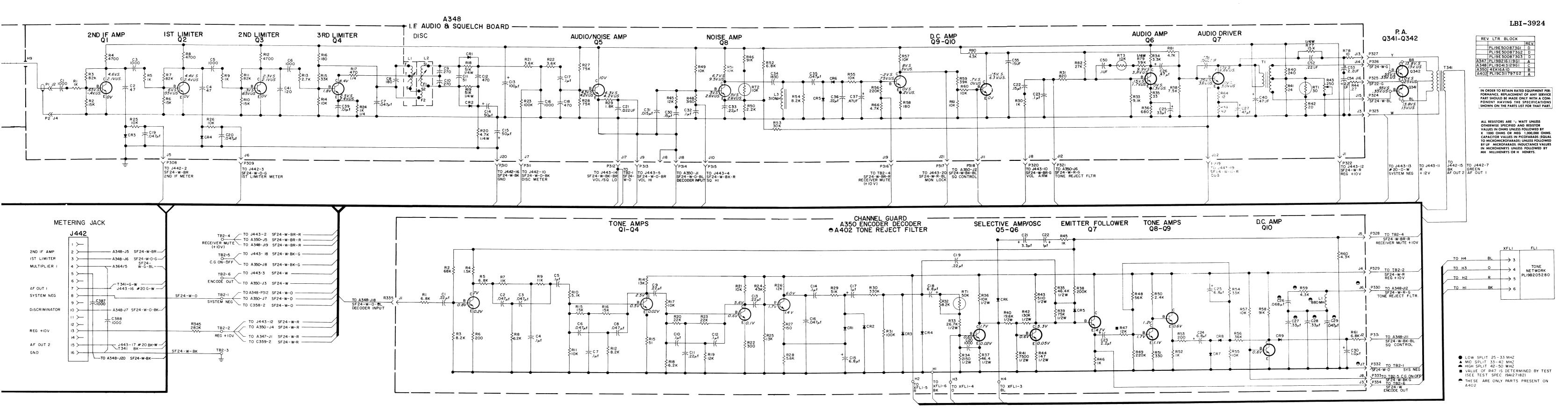
SCHEMATIC DIAGRAM

Issue 4

25—50 MHz RECEIVER MODELS 4ER39C10-27

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(19R621227, Rev. 14)

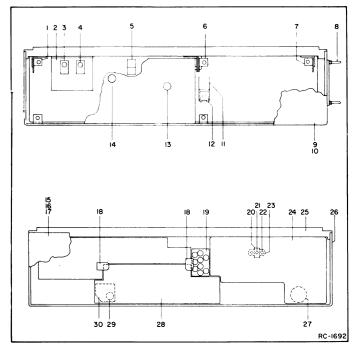


(19R621227, Rev. 14)

SCHEMATIC DIAGRAM

25-50 MHz RECEIVER MODELS 4ER39C10-27

4	SYMBOL GE PART NO.	DESCRIPTION	SYMBO	L G-E PART NO	DESCRIPTION	SYMBO	L G-E PART NO	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBO	L G-E PART NO	DESCRIPTION	SYMBOL	G-E PART NO	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	1 2 3
	R20 3R152-P223J R21 3R152-P103J	Composition: 22,000 ohms ±5%, 1/4 w. Composition: 10,000 ohms ±5%, 1/4 w.	RT1	5490828-P22	THERMISTORS Thermistors: 50,000 ohms ±10%, color code yellow:	R11 and R12	3R152~P102J	Composition: 1000 ohms ±5%, 1/4 w.	C13	5491601-P137 5491601-P114	Tubular: 0.91 pf ±5%, 500 VDCW. Tubular: 0.51 pf ±5%. 500 VDCW.	L341		INDUCTORS	Z341		TUNED CIRCUITS			CHANNEL GUARD MODIFICATION KIT 19A127178-G2	
	R22 3R152-P301J R23 3R152-P223J	Composition: 300 ohms ±5%, 1/4 w. Composition: 22,000 ohms ±5%, 1/4 w.			sim to Globar Type 763H.	R14 R15	3R 152-P103J 3R 152-P101K	Composition: 10,000 ohms ±5%, 1/4 w. Composition: 100 ohms ±10%, 1/4 w.	C15	5491601-P115	Tubular: 0.56 pf ±5%, 500 VDCW.	thru L346		COIL ASSEMBLY L341 19B204820-G5 (4ER39C10, 13, 16, 19,22,25) L342 19B204820-G6 (4ER39C10, 13, 16, 19,22,25)	thru Z343		Z341 19B204786-G1 Z342 19B204786-G2			(Used with A402)	
	R24 3R152-P433J	Composition: 43,000 ohms ±5%, 1/4 w.	XFL1	19A121920-G3	Reed, mica-filled phen: 7 pins rated at 1 amp at	R19	3R 15 2-P360J	Composition: 36 ohms ±5%, 1/4 w.	C16	5491601-P130	Tubular: 3.3 pf ±5%, 500 VDCW.			L343 19B204820-G1 (4ER39C11, 14, 17, 20,23,26) L344 19B204820-G2 (4ER39C11, 14, 17, 20,23,26)			Z343 19B204786-G3		19B216177-G1	MISCELLANEOUS	
	R25 3R152-P133J	Composition: 13,000 ohms ±5%, 1/4 w.	1		500 VRMS with 4-1/2 inches of cable.	R21	3R 15 2-P750J	Composition: 75 ohms ±5%, 1/4 w.	CR1	4038056-P1	DIODES AND RECTIFIERS			L345 19B204820-G3 (4ER39C12, 15, 18, 21,24,27) L346 19B204820-G4 (4ER39C12, 15, 18, 21, 24,27)	C1	5496218-P254		P321	4029840-P2	Contact, electrical; sim to Amp 42827-2.	
	R26 3R152-P123J R27 3R152-P151J	Composition: 12,000 ohms ±5%, 1/4 w. Composition: 150 ohms ±5%, 1/4 w.	A352 thru	ļ	FIRST OSCILLATOR ASSEMBLY		ļ	THERMISTORS	CRI	4038056-PI	Germanium			CAPACITORS			-80 PPM.	P330	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.	
	R28 3R152-P562J	Composition: 5600 ohms ±5%, 1/4 w.	A357		A352 19B204419-G13 (4ER39A10, 19) A353 19B204419-G16 (4ER39C11, 12, 20, 21) A354 19B204419-G14 (4ER39C13, 22)	RT1 thru	19B209284-P5	Disc: 43 ohms res nominal at 25°C, color code green.	Rl	3R 15 2-P4 73 K	Composition: 47,000 ohms ±10%, 1/4 w.	C341	19B209159-P3	Variable, subminiature: approx 1.70-6.9 pf, 750 v peak; sim to EF Johnson 189-3-59. (Used	C2	5496218-P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	P332	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.	
	R29 3R152-P513J	Composition: 51,000 ohms ±5%, 1/4 w.		1	A355 19B204419-G17 (4ER39C14, 15, 23, 24) A356 19B204419-G15 (4ER39C16 25)	RT4						C342	19B209159-P3	in L341, L343 and L345). Variable, subminiature: approx 1.70-6.9 pf.	C3	5496218-P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.			MECHANICAL PARTS	15
	R30 3R152-P334J R31 3R152-P104J	Composition: 0.33 megohms ±5%, 1/4 w. Composition: 0.1 megohms ±5%, 1/4 w.		İ	A357 19B204419-G18 (4ER39C17, 18, 26, 27)	тэ			Т1	19B205325-G2	Coil, includes tuning slug 5491798-P4.			750 v peak; sim to EF Johnson 189-3-59. (Used in L342, L344 and L346).	C4	5494481-P14	Ceramic disc: .002 µf ±10%, 500 VDCW; sim to RMC Type JF Discap.			(SEE RC-1692)	17
	R32 3R152-P822J	Composition: 8200 ohms ±5%, 1/4 w.		5494481-P112	CAPACITORS	and T4		COIL ASSEMBLY T3 19B205416-G1 T4 19B205416-G2	T2 and	19 B205 325- GI	Coil, includes tuning slug 5491798-P4.			INDICATING DEVICES]	i	MI SCELLANEOUS	1	19B204583-G3 19B216727-P1	Hinge,	
	R33 19A116278-P34	Metal film: 26,700 ohms ±2%, 1/2 w.	thru C4	3454461=P112	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.				T4	19B205325-G2	Coil, includes tuning slug 5491798-P4.	DS301	19B209067-P1	Lamp, glow: 0.3 ma; sim to GE NE-2T.		5491798-P1	Tuning slug. (Used in Z341).	3	19A116023-P2	Support. (Used with Q341 and Q342). Plate, insulated. (Used with Q341 and Q342).	
	R34 19A116278-P23 R35 19A116278-P36	Metal film: 2150 ohms ±2%, 1/2 w.	C5 thru	5496219-P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.	C34	5496218-P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef	T5 and	19B205325-G1	Coil, includes tuning slug 5491798-P4.					5491798-P4	Tuning slug. (Used in Z342).	4	19 Al 16022-Pl	Insulator. (Used with Q341 and Q342).	
	R36 19A116278-P30	Metal film: 46,400 ohms ±2%, 1/2 w. Metal film: 10,000 ohms ±2%, 1/2 w.	C8	5401051 5100		C35	5496218-P249	-80 PPM. Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef	T6			P301 thru	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.		5491798-P5	Tuning slug. (Used in Z343).	5	40 29 851-P6	Clip, loop.	
	R37 19A116278-P65	Metal film: 46.4 ohms ±2%, 1/2 w.	thru C12	5491271-P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189-6-5.			-80 PPM.	A402		TONE REJECT FILTER 19C311797-G2	P313	40,000,000		Z347 thru		COIL ASSEMBLY	7	19B204583-G1 19B204583-G2	Hinge.	
	R38 3R152-P204J R39 19A116278-P38	Composition: 0.2 megohm ±5%, 1/4 w.	C13	5496219-P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef						REV A	P315 thru P317	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.	Z349		Z347 19B204767-G1 Z348 19B204767-G2 Z349 19B204767-G3	8	19 Al 21676-Pl	Guide pin.	
	R39 19Al16278-P38 R40 19Al16278-P32	Metal film: 75,000 ohms ±2%, 1/2 w. Metal film: 19,000 ohms ±2%, 1/2 w.	thru C16			L4	19 A1 21 46 4-P1	Coil. Includes tuning slug 5491798-P5.			CAPACITORS	P319	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.				9	19C303396-G4	Bottom cover. (Station)	
	R41 19A116278-P28	Metal film: 7500 ohms ±2%, 1/2 w.	C17 thru C20	19C300685-P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.	XY1		SOCKETS	C26 C27	19A116080-P206 19A116080-P210	,	and P320			C1	5496218-P254	CAPACITORS	10	19C303385-G1 19A121297-P1	Bottom cover. (Mobile) Angle.	
	R42 19A116278-P41	Metal film: 130,000 ohms ±2%, 1/2 w.	C21	5496219-P771	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef	thru XY4		Refer to Mechanical Parts (RC-1692).	and C28		701yester. 0.35 µ1 15%, 50 VICH.	P322 P323	40 29 84 0-P2 40 29 84 0-P1	Contact, electrical; sim to Amp 42827-2. Contact, electrical; sim to Amp 41854.	C2	5496218-P250	-80 PPM.	12	71 60 86 1-P4	Nut. (Used to secure cover).	
	R43 19A116278-P26 R44 19A116278-P11	Metal film: 5110 ohms ±2%, 1/2 w. Metal film: 147 ohms ±2%, 1/2 w.	C22	5496219-P773	-750 PPM. Ceramic disc: 270 pf ±5%, 500 VDCW, temp coef			CRYSTALS	C29*	19A116080-P205	Polyester: 0.047 µf ±5%, 50 VDCW. Earlier than REV A:	P324	40 29 84 0-P2	Contact, electrical; sim to Amp 42827-2.	11		Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.	13	4036555-P1	Insulator disc. (Used with Q7 on A348).	
	R45 3R152-P102J	Composition: 1000 ohms ±5%, 1/4 w.	C23	5494481-P114	-750 PPM. Ceramic disc: .002 µf ±10%, 1000 VDCW; sim to			When reordering give GE Part No. and specify exact freq needed.		19B209243-P107	Polyester: 0.1 μf ±10%, 50 VDCW.	P325	4029840-P1	Contact, electrical; sim to Amp 41854.	СЗ	5496218-P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	14	40 35 26 7- P2 19 C3 03 49 5- G3	Button, plug. (Used with A348, A350 and A402). Top cover. (Station, except Repeaters and VM).	
	R46		C26		RMC Type JF Discap.			25-42 MHz crystal freq = (OF +5.30 MHz) ÷ 3.			JACKS AND RECEPTACLES	P326 P327	4029840-P2 4029840-P1	Contact, electrical; sim to Amp 42827-2. Contact, electrical; sim to Amp 41854.			MI SCELLANEOUS	16	19C303676-G2	Top cover. (Station, Repeaters and VM only).	
		NOTE The value of Resistor R47 must be obtained from the component, then find corresponding value	thru C28	5494481-P112	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	V1	19B206576-P1	42-50 MHz crystal freq = (OF -5.30 MHz) ÷ 3. Quartz: freq range 10086.666 to 12766.666 KHz.	J6 and J7	4033513-P4	Contact, electrical; sim to Bead Chain L93-3.					5491798-P1	Tuning slug. (Used in Z347).	17	19C3O3385-G2	Top cover. (Mobile)	
	R47A 3R152-P822J	in parts list for the correct part number.	C31	5494481-P112	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	thru Y4		temp range -30°C to +85°C. (25-33 MHz).				Q341*	19 Al 16 20 3-P2	TRANSISTORS Silicon, NPN.		5491798-P4 5491798-P5	Tuning slug. (Used in Z348). Tuning slug. (Used in Z349).	18	40 29 85 1-P3 19 A1 21 383-P1	Clip, loop. Support.	
	R47B 3R152-P912J	Composition: 8200 ohms ±5%, 1/4 w. Composition: 9100 ohms ±5%, 1/4 w.	C45	5490008-P35	Silver mica: 220 pf ±5%, 500 VDCW.	Y1 thru	19B206576-P2	Quartz: freq range 12766.667 to 15766.666 KHz, temp range -30°C to +85°C. (33-42 MHz).	L1	19Al15690-Pl	Coil, RF: 880 mh ±5%, sim to Artted AC5672.	and Q342*	19Al15948-Pl	Earlier than REV B: Silicon, NPN,	7250			20	4033089-P1	Clip (Part of XY1-XY4).	
	R47C 3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.	C46	5496219-P563	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef	Y4	19B206576-P3	Quartz: freq range 12233,333 to 16233,333 KHz.			RESISTORS			,	Z350 thru Z352		COIL ASSEMBLY Z350 19B204784-G4	21	19B200525-P9	Rivet (Part of XY1-XY4).	
	R47D 3R152-P113J R47E 3R152-P123J	Composition: 11,000 ohms ±5%, 1/4 w.		ł	DYODES AND DESCRIPTIONS	thru Y4	198200370-23	temp range -30°C to +85°C. (42-54 MHz).	R59	3R152-P432J	Composition: 4300 ohms ±5%, 1/4 w.	R343	3R152-P101K				Z351 19B204784-G5 Z352 19B204784-G6	22	19 A1 15 79 3- P1 19 C3 11 17 2- P1	Contact. (Part of XY1-XY4). Crystal socket. (Part of XY1-XY4).	
	R47F 3R152-P133J	Composition: 12,000 ohms ±5%, 1/4 w. Composition: 13,000 ohms ±5%, 1/4 w.	CR1	19A115348-P1	DIODES AND RECTIFIERS Silicon.	A364		MULTIPLIER SELECTIVITY ASSEMBLY			CHASSIS AND RF ASSEMBLY 19E500873-G1 thru G3	and R344					CAPACITORS	24	19C303547-P1	Cover.	
	R47G 3R152-P153J	Composition: 15,000 ohms ±5%, 1/4 w.	thru CR3	1		and A365		A364 19B205326-G1 (4ER39A10, 13, 16, 19, 22,			REV B	R345*	5495948-P444	Deposited carbon: 280,000 ohms ±1%, 1/2 w; sim to Texas Instrument CD1/2MR. Added by REV B.	C7 and	5496218-P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	25	19C317344-P3	Heat sink.	
	R47H 3R152-P752J	Composition: 7500 ohms ±5%, 1/4 w.		4033513-P4	JACKS AND RECEPTACLES			A365 19B205326-G2 (4ER39A11, 12, 14, 15, 17, 18, 20, 21, 23, 24,	22.40	5401001 7774		R346*	3R 78-P390K	Composition: 39 ohms ±10%, 1 w. Added by REV B.	C8	5496218-P244	County days 15 to 150 to 150	26	19C303389-G1	Chassis.	
	R48 3R152-P563J R49 3R152-P224J	Composition: 56,000 ohms ±5%, 1/4 w. Composition: 0.22 megohms ±5%, 1/4 w.	J1 thru J6	4033313-P4	Contact, electrical: sim to Bead Chain L93-3.			26, 27)	C349 C350	5491601-P114 5491601-P110	Tubular: 0.51 pf ±5%, 500 VDCW. Tubular: 0.36 pf ±5%, 500 VDCW.			TRANSFORMERS	11		Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -80 PPM.	28	4034252-P5 19B204672-P1	Can (Used with Tl on A347). Cover.	
	R50 3R152-P242J	Composition: 2400 ohms ±5%, 1/4 w.			IN DUCTORS		5406010 2050		and C351		,	T341	19A116041-P1	Audio freq: 300 to 4000 Hz, Pri: 1.00 ohms ±15% DC res,	C10	5494481-P7	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	29	7162414-P1	Retainer, transistor. (Used with Q1 on A341).	
	R51 3R152-P331J	Composition: 330 ohms ±5%, 1/4 w.	L2 and	7488079-P16	Choke, RF: 10 µh ±10% ind at 640 ma, 0.6 ohm DC res; sim to Jeffers 4421-7.	and C2	5496218-P252	Ceramic disc: 36 μf ±5%, 500 VDCW, temp coef -80 PPM.	C358 thru	5493392-P7	Ceramic feed-thru: .001 µf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.			Sec 1: .23 ohm ±10% DC res, Sec 2: 10.5 ohms ±15% DC res.			MISCELLANEOUS	30	19B204917-P2	Support.	
	R52 3R152-P102J R53 3R152-P201J	Composition: 1000 ohms ±5%, 1/4 w. Composition: 200 ohms ±5%, 1/4 w.	LS			сз	5496218-P251	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef	C363 C385	7774750- P 4	Ceramic disc: .001 µf +100% -0%, 500 VDCW.			TERMINAL BOARDS		5491798~P1	Tuning slug. (Used in Z350).				
	R54 3R152-P333J	Composition: 33,000 ohms ±5%, 1/4 w.	Q1	19 Al 15330-Pl	TRANSISTORS	C4	5496218-P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef	C387	5494481-P12	Ceramic disc: .001 µf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	TB1	7487424-P26	Miniature, phen: 6 terminals.		5491798-P4 5491798-P5	Tuning slug. (Used in Z351). Tuning slug. (Used in Z352).			****************	
	R55 3R152-P103J	Composition: 10,000 ohms ±5%, 1/4 w.	and Q2		,	C5		-ou ppm.	C388		,ye or biscap.						1				
	R56 3R152-P363J R57 3R152-P103K	Composition: 36,000 ohms ±5%, 1/4 w. Composition: 10,000 ohms ±10%, 1/4 w.			RESISTORS	C6	5496218-P247	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef -80 PPM.			DIODES AND RECTIFIERS	W442	19B205634-06	Coaxial: approx 5 inches long.			CHANNEL GUARD MODIFICATION KIT 19A127178-G1 (Used with A350)				
	R58 3R152-P913J	Composition: 91,000 ohms ±5%, 1/4 w.	Rl thru R4	3R 15 2-P56 2J	Composition: 5600 ohms ±5%, 1/4 w.	C7 and	5493392-P107	Ceramic feed-thru: 470 pf +100% - 0%, 500 VDCW.	CR1	19 A1 16 06 2-P2	Thyrector.	W443	19B205634-G3	Coaxial: approx 5 inches long.			MI SCELLANEOUS				
	R59 3R152-P432J and	Composition: 4300 ohms ±5%, 1/4 w.	R5	3R 152-P104K	Composition: 0.1 megohm ±10%, 1/4 w.	C8 C9	5491601-P123	Tubular: 1.5 pf ±5%, 500 VDCW,	1		JACKS AND RECEPTACLES					19B216176-G1	Harness (Encoder/Decoder). Includes:				
	R60 R61 3R152-P682K	Composition: 6800 ohms ±10%, 1/4 w.	thru R8			C10	5491601-P117	Tubular: 0.68 pf ±5%, 500 VDCW.	J442	19B205689-G2	Connector: 18 contacts rated at 5 amps min at 1000 VDC max.				P314	4029840-P2	Contact, electrical; sim to Amp 42827-2.				
	311021021	27-28-21-2011. 3000 Silms 110/8, 1/4 W.	R9 R10	3R152-P153J 3R152-P101K	Composition: 15,000 ohms ±5%, 1/4 w.	C11	5491601-P118	Tubular: 0.75 pf ±5%, 500 VDCW.	J443	19C303426-G1	Connector: 20 pin contacts.				P318 P321	4029840-P2 4029840-P2	Contact, electrical; sim to Amp 42827-2.				
			RIO	3K152-P101K	Composition: 100 ohms ±10%, 1/4 w.	C12	5491601-P132	Tubular: 4.7 pf ±5%, 500 VDCW.							P328	4029840-P2 4029840-P2	Contact, electrical; sim to Amp 42827-2. Contact, electrical; sim to Amp 42827-2.				
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PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - 2nd Mixer A347 (19B216119-G1)

To make receivers compatible with solid-state transmitters. Added C17.

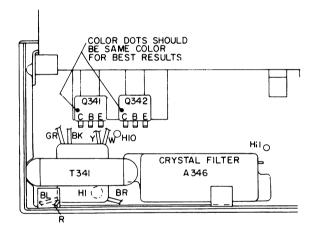
REV. A - 19E500873-G1 thru -G3 (Chassis & RF Assembly)

To protect the receiver against positive voltage transients. Added thyrector CR1 between J443-11 and J443-13.

REV. B - 19E500873-G1 thru -G3 (Chassis & RF Assembly)

To incorporate new PA transistors. Changed Q341 and Q342 and added R346.

OUTLINE DIAGRAM WAS:



REV. C - 1st Osc/Mult A352 & A353

REV. A - 1st Osc/Mult A354 thru A357

These revisions incorporated into initial shipment.

REV. A - Channel Guard Encoder/Decoder A350 (Model 4EK16A10)

To obtain correct output level. Changed R8.

REV. B - Channel Guard Encoder/Decoder A350 (Model 4EK16A10)

To increase stop-band attenuation. Changed R8.

REV. C - Channel Guard Encoder/Decoder A350 (Model 4EK16A10)
REV. A - Tone Reject Filter A402 (19C311797-G2)

To optimize frequency response. Changed C29.

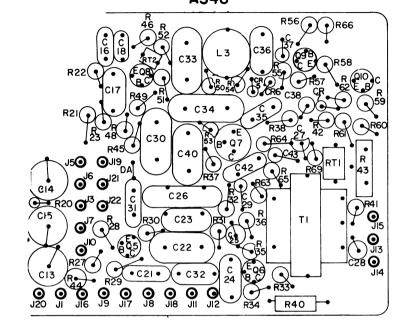
LBI-3924

REV. A - IF Audio & Squelch Board A348 (19D413129-G1)

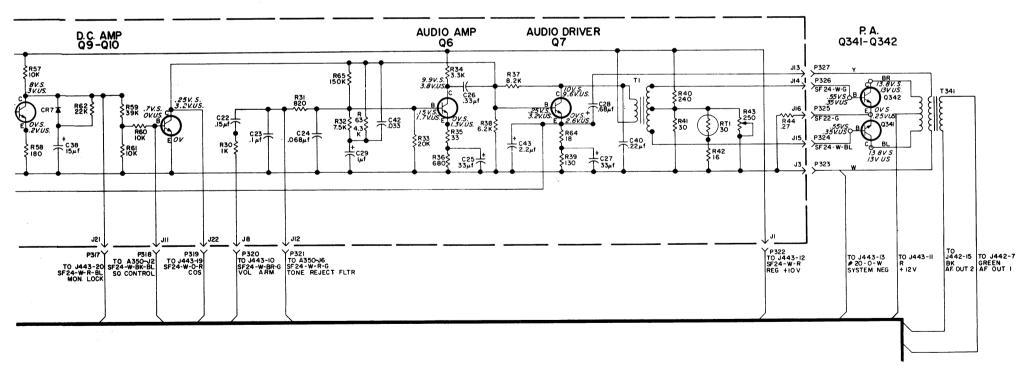
To make IF Audio & Squelch Board compatible with new PA transistors and to improve squelch operation. Added C49-C54, CR8, R75-R79, and RT3. Deleted C24, C28, C29, C42, C43, R32, R37, R63 and R65. Changed C21, C26, C37, C38, C40, R33, R38, R39, R41, R42, R48, R53 and R62.

Outline Diagram Was:

IF-AUDIO & SQUELCH BOARD



Schematic Diagram Was:



PRODUCTION CHANGES

25-50 MHz MASTR RECEIVER MODELS 4ER39C10-27

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REV. C - Chassis and RF Assembly (19E500873-G1 thru -G3)

To eliminate squelch opening thump in receivers with Channel Guard. Remove White-Orange wire between J443-13 and TB2-1. Added a White-Orange wire between P312 (or J17 on IF Audio and Squelch board) and TB2-1.

REV. B - IF Audio & Squelch Board A348 (19D413129-G1)

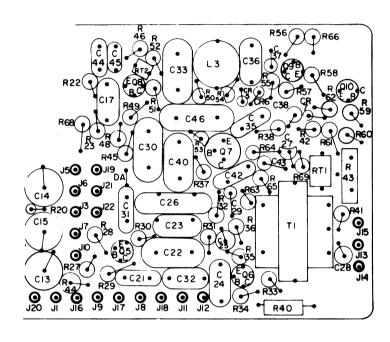
To control more closely the squelch control rotation. Changed R48.

REV. C - IF Audio & Squelch Board A348 (19D413129-G1)

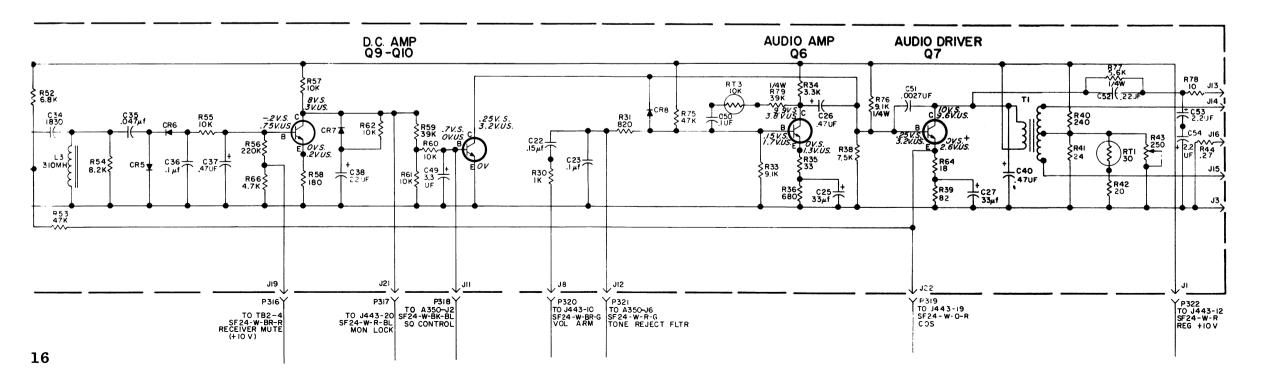
To eliminate barely audible squelch switching transients and to reduce receiver squelch tail. Deleted C38, C49, CR7, CR8, R62, R75, and R76. Added C55, R80, R81, and R82. Changed C27, C36, R53, R64, and R77.

Outline Diagram Was:

IF-AUDIO & SQUELCH BOARD



Schematic Diagram Was:



ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- GE Part Number for component
 Description of part
- 3. Model number of equipment
- 4. Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

MOBILE RADIO DEPARTMENT LYNCHBURG, VIRGINIA 24502 CABLE GECOMPROD (In Canada, Canadian General Electric Company, Ltd., 100 Wingold Avenue, Toronto 19, Ontario)